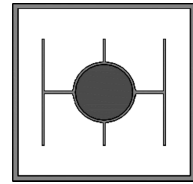


High-Power 14 mil (0.35mm) IR LED CHIP (980nm)

Type : YL-C980nM-7.6mW



1. Description

14 mil(typ.) High-Power LED chip, N-side up, peak wavelength is 980nm(typ.)

2. Physical Characteristics and Structure

- 1) Material : InAlGaAs-Epitaxial Layer and Silicon-Substrate
- 2) Die Size (typ.) : 0.350mm × 0.350mm (14 mil)
- 3) Thickness (typ.) : 0.180 mm (7 mil)
- 4) Bond Pad Size : 0.100mm diameter (periphery = 0.110mm diameter)
- 5) Anode Metallization : Gold-Alloy
- 6) Cathode Metallization : Gold-Alloy

3. Electro-Optical Characteristics

(Ta = 25°C. LED-chip is mounted on TO-18 gold stem without resin coated)

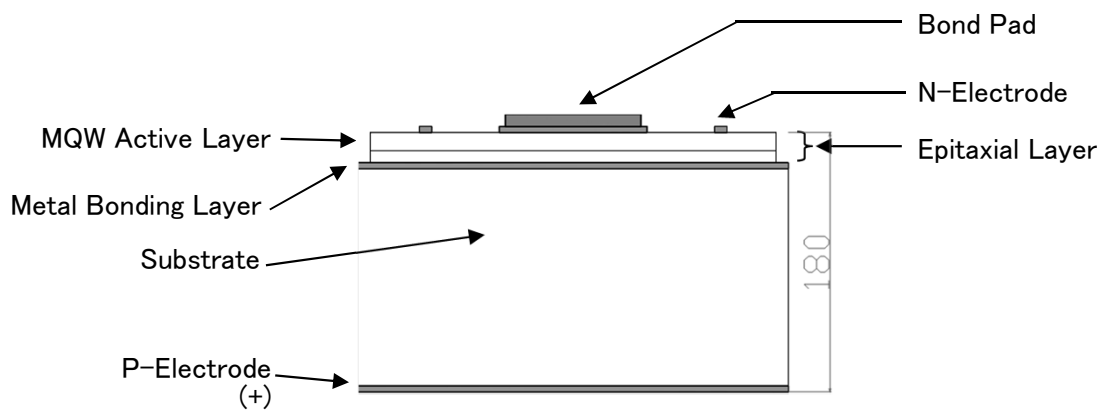
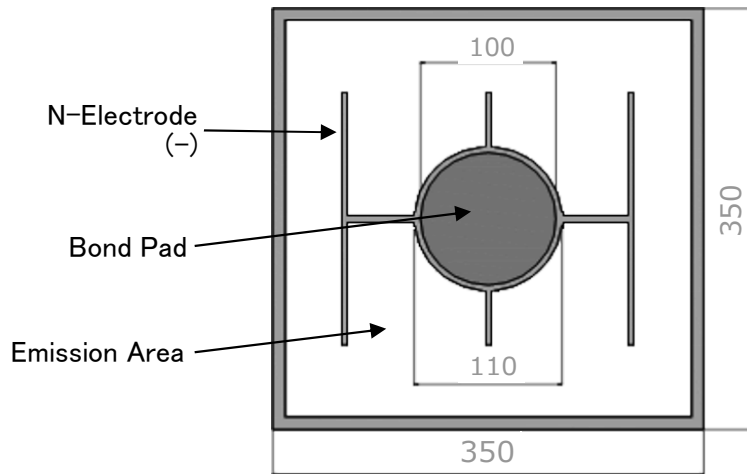
Parameter	Symbol	Condition	Value			Unit
			min.	typ.	max.	
Forward Voltage	V _f	I _f = 20 mA		1.27		V
Reverse Current	I _r	V _r = 5 V			10	μ A
Radiant Power	P _o	I _f = 20 mA		7.6		mW
Peak Wavelength	λ _p	I _f = 20 mA		987		nm
Full Width at Half Max.	Δ λ	I _f = 20 mA		31		nm

Remark: This specification is for reference purpose only, and subject to change without prior notice.
Approved specification shall be obtained for the regular purchase.

High-Power 14 mil (0.35mm) IR LED CHIP (980nm)

Type : YL-C980nM-7.6mW

4.Physical Dimensions



(Unit: μ m)

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